## SPICE Device Model SiHU6N62E



**Vishay Siliconix** 

## **E Series Power MOSFET**

### DESCRIPTION

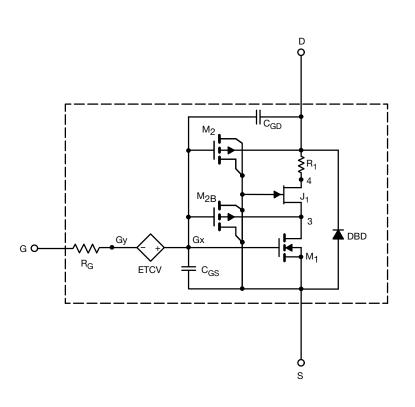
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to 150 °C temperature ranges under the pulsed 0 V to 15 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}\xspace$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

### SUBCIRCUIT MODEL SCHEMATIC



#### Note

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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| <b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |  |                   |                  |      |
|--|---------------------|--|-------------------|------------------|------|
| PARAMETER  | SYMBOL              | TEST CONDITIONS  | SIMULATED<br>DATA | MEASURED<br>DATA | UNIT |
| Static   |                     |  |                   |                  |      |
| Gate Threshold Voltage   | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$  | 3                 | -                | V    |
| Drain-Source On-State Resistance <sup>a</sup>                          | R <sub>DS(on)</sub> | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$                                 | 1.5               | 0.78             | Ω    |
| Forward Transconductance <sup>a</sup>                                  | 9 <sub>fs</sub>     | $V_{DS} = 30 \text{ V}, \text{ I}_{D} = 3 \text{ A}$                                 | 1.8               | 1.8              | S    |
| Diode Forward Voltage  | V <sub>SD</sub>     | $I_{S} = 3 \text{ A}, V_{GS} = 0 \text{ V}$  | 0.80              | 0.90             | V    |
| Dynamic <sup>b</sup>   |                     |  |                   |                  |      |
| Input Capacitance  | C <sub>iss</sub>    | $V_{DS}$ = 100 V, $V_{GS}$ = 0 V, f = 1 MHz  | 678               | 578              | pF   |
| Output Capacitance   | Coss                |  | 39                | 36               |      |
| Reverse Transfer Capacitance   | C <sub>rss</sub>    |  | 4                 | 4                |      |
| Total Gate Charge  | Qg                  |  | 17                | 17               |      |
| Gate-Source Charge   | Q <sub>gs</sub>     | $V_{DS} = 496 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$ | 4                 | 4                | nC   |
| Gate-Drain Charge  | Q <sub>gd</sub>     |  | 8                 | 8                |      |

#### Notes

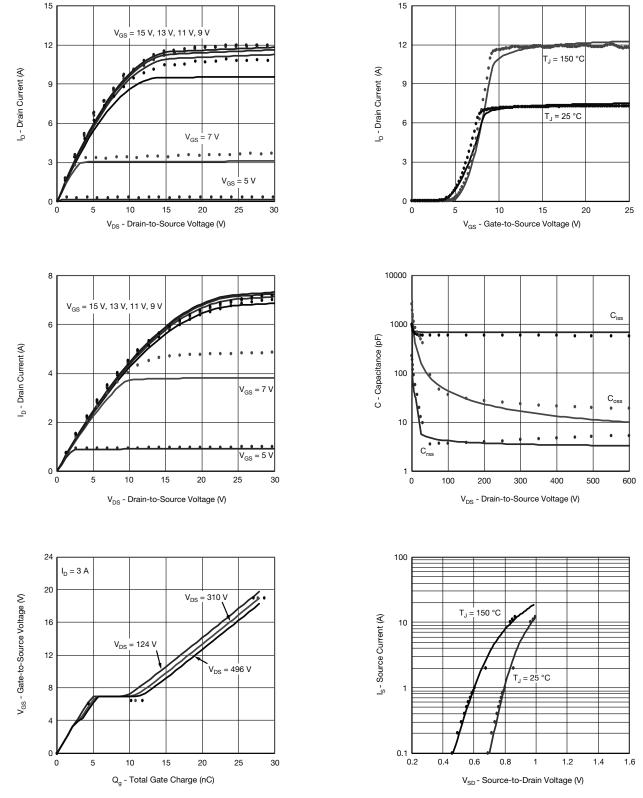
a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.



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### COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)



#### Note

• Dots and squares represent measured data. Copyright: Vishay Intertechnology, Inc.

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